

# HAT1108C

## Silicon P Channel MOS FET Power Switching

REJ03G1234-0400

Rev.4.00

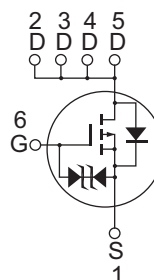
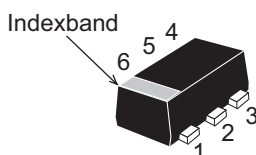
Jun. 13, 2005

### Features

- Low on-resistance  
 $R_{DS(on)} = 155 \text{ m}\Omega$  typ. (at  $V_{GS} = -10 \text{ V}$ )
- Low drive current.
- 4.5 V gate drive devices.
- High density mounting

### Outline

RENESAS Package code: PWSF0006JA-A  
(Package name: CMFPAK-6)



1. Source
2. Drain
3. Drain
4. Drain
5. Drain
6. Gate

### Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Drain to Source voltage	$V_{DSS}$	-30	V
Gate to Source voltage	$V_{GSS}$	+20/-10	V
Drain current	$I_D$	-1.5	A
Drain peak current	$I_D$ (pulse) <sup>Note 1</sup>	-6	A
Body - Drain diode reverse drain current	$I_{DR}$	-1.5	A
Channel dissipation	$P_{ch}$ <sup>Note 2</sup>	830	mW
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Notes 1.  $PW \leq 10 \mu\text{s}$ , duty cycle  $\leq 1\%$

2. When using the glass epoxy board. (FR4  $40 \times 40 \times 1.6\text{mm}$ ),  $T_a = 25^\circ\text{C}$

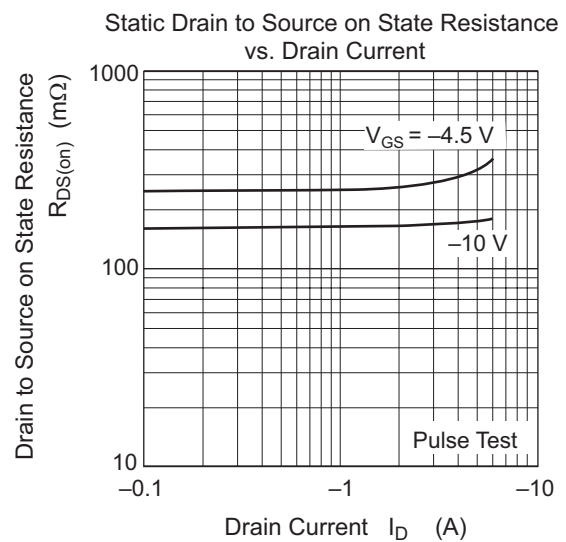
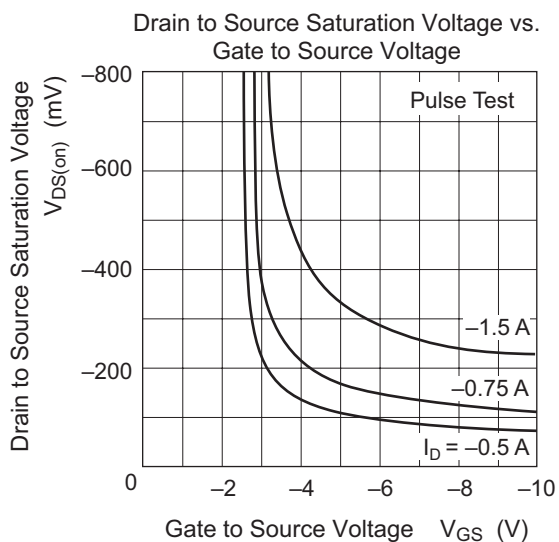
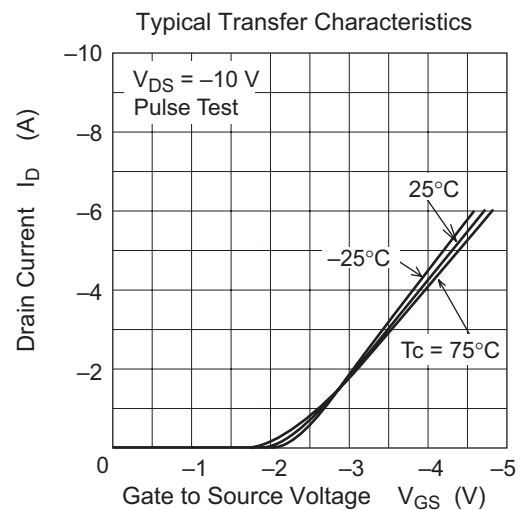
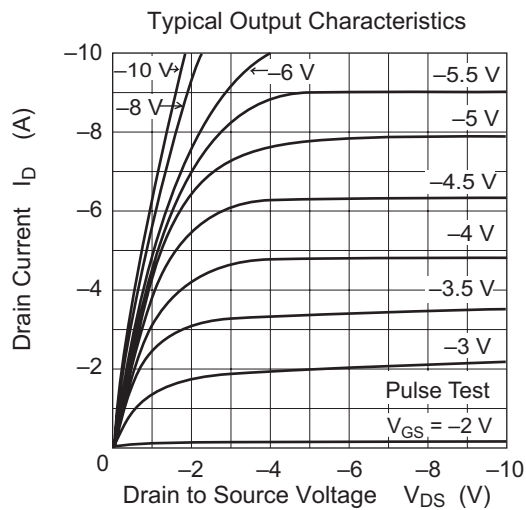
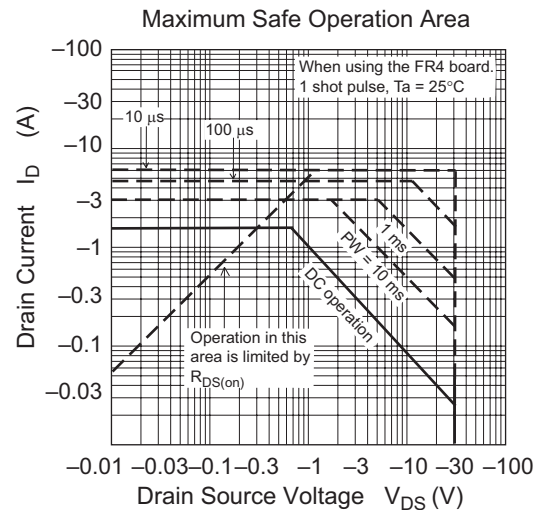
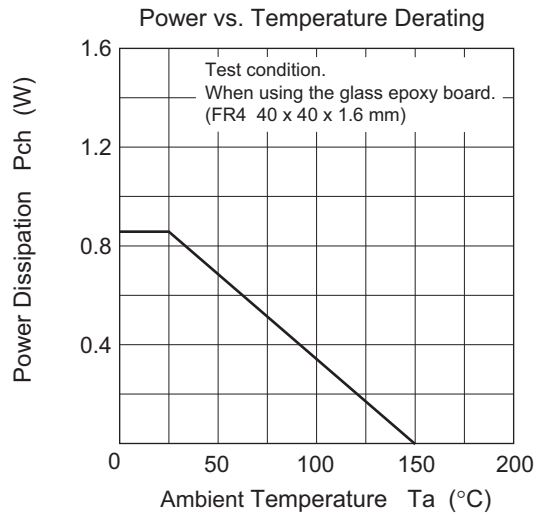
## Electrical Characteristics

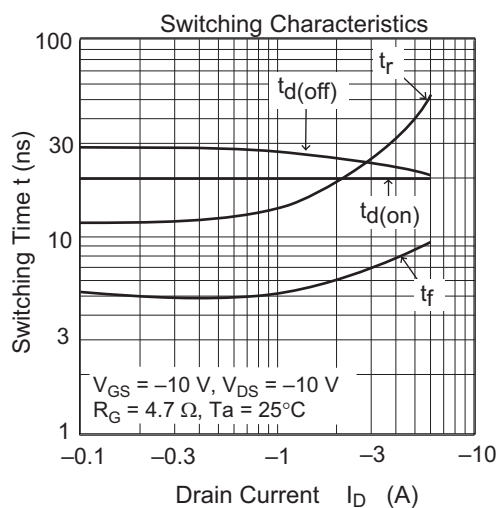
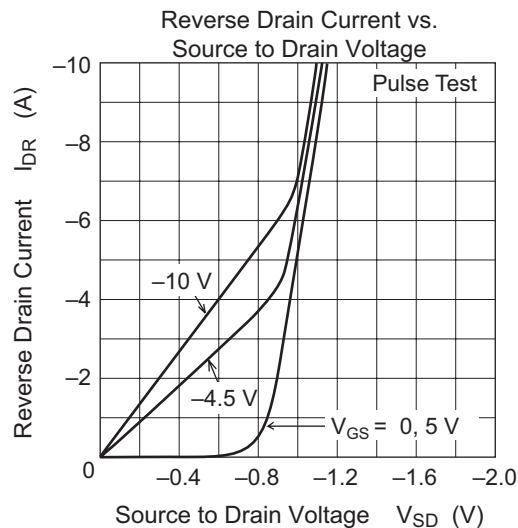
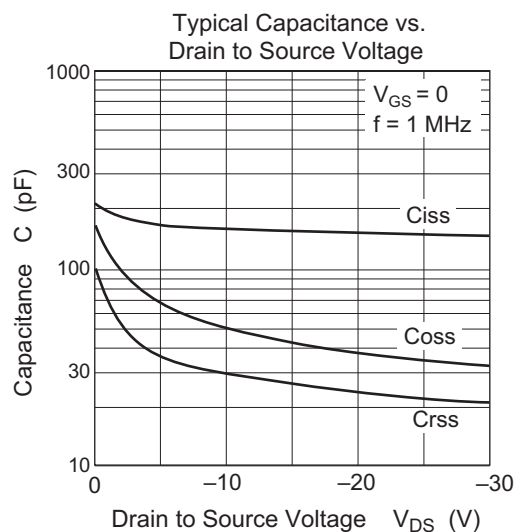
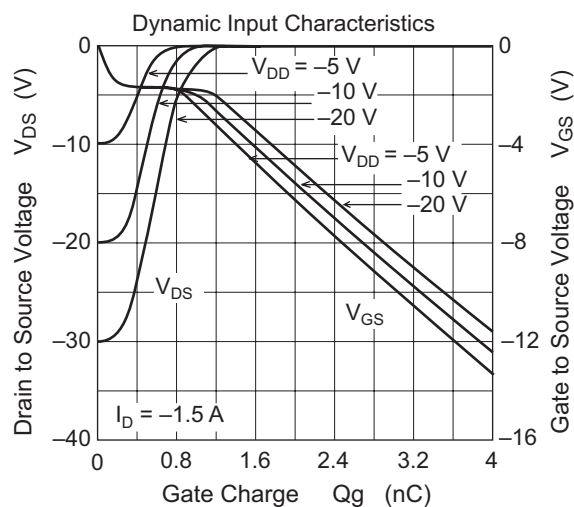
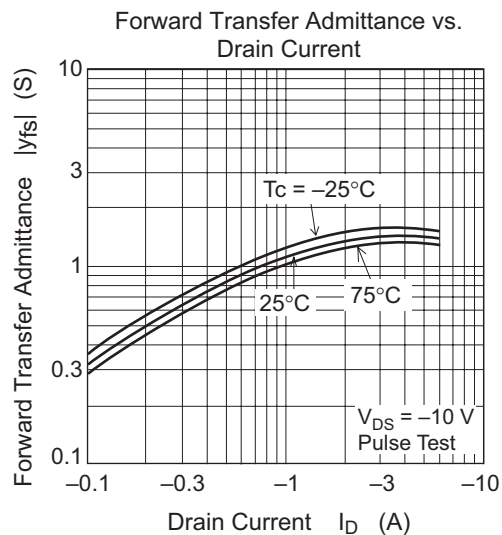
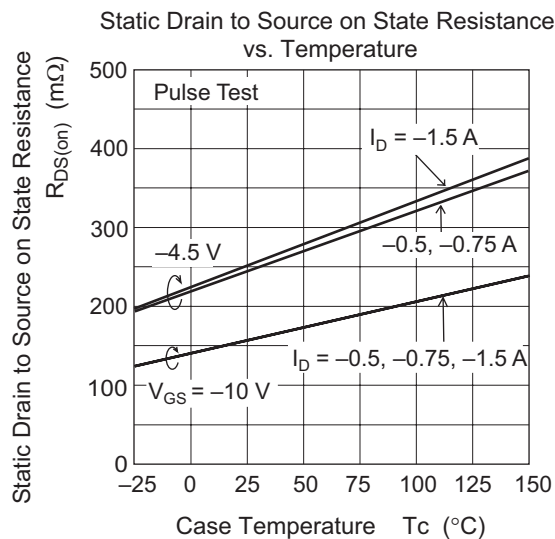
(Ta = 25°C)

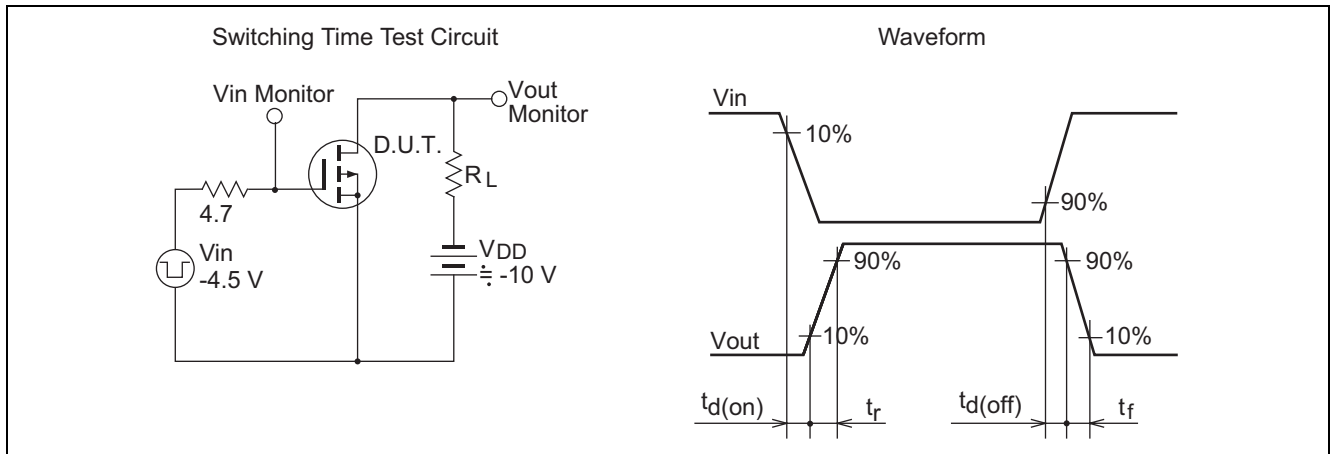
Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -10 \text{ mA}$ , $V_{GS} = 0$
Gate to Source breakdown voltage	$V_{(BR)GSS}$	-20 +10	—	—	V	$I_G = \pm 100 \mu\text{A}$ , $V_{DS} = 0$
Gate to Source leakage current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = -16/ +8 \text{ V}$ , $V_{DS} = 0$
Drain to Source leakage current	$I_{DSS}$	—	—	-1	$\mu\text{A}$	$V_{DS} = -30 \text{ V}$ , $V_{GS} = 0$
Gate to Source cutoff voltage	$V_{GS(th)}$	-0.5	—	-2.0	V	$I_D = -1 \text{ mA}$ , $V_{DS} = -10 \text{ V}$ <sup>Note4</sup>
Drain to Source on state resistance	$R_{DS(on)}$	—	155	194	$\text{m}\Omega$	$I_D = -0.75\text{A}$ , $V_{GS} = -10 \text{ V}$ <sup>Note4</sup>
		—	245	356	$\text{m}\Omega$	$I_D = -0.75\text{A}$ , $V_{GS} = -4.5 \text{ V}$ <sup>Note4</sup>
Forward transfer admittance	$ y_{fs} $	0.65	1	—	S	$I_D = -0.75\text{A}$ , $V_{DS} = -10 \text{ V}$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	160	—	pF	$V_{DS} = -10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	50	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	30	—	pF	
Total gate charge	$Q_g$	—	3	—	nC	$V_{DS} = -10 \text{ V}$ , $V_{GS} = -10 \text{ V}$ , $I_D = -1.5 \text{ A}$
Gate to Source charge	$Q_{gs}$	—	0.2	—	nC	
Gate to Drain charge	$Q_{gd}$	—	0.6	—	nC	
Turn - on delay time	$t_{d(on)}$	—	20	—	ns	$V_{DS} = -10 \text{ V}$ , $V_{GS} = -10 \text{ V}$ , $I_D = -0.75 \text{ A}$ , $R_L = 13.3 \Omega$ , $R_g = 4.7 \Omega$
Rise time	$t_r$	—	13	—	ns	
Turn - off delay time	$t_{d(off)}$	—	28	—	ns	
Fall time	$t_f$	—	5	—	ns	
Body - Drain diode forward voltage	$V_{DF}$	—	-0.85	-1.2	V	$I_F = -1.5 \text{ A}$ , $V_{GS} = 0$

Notes: 4. Pulse test

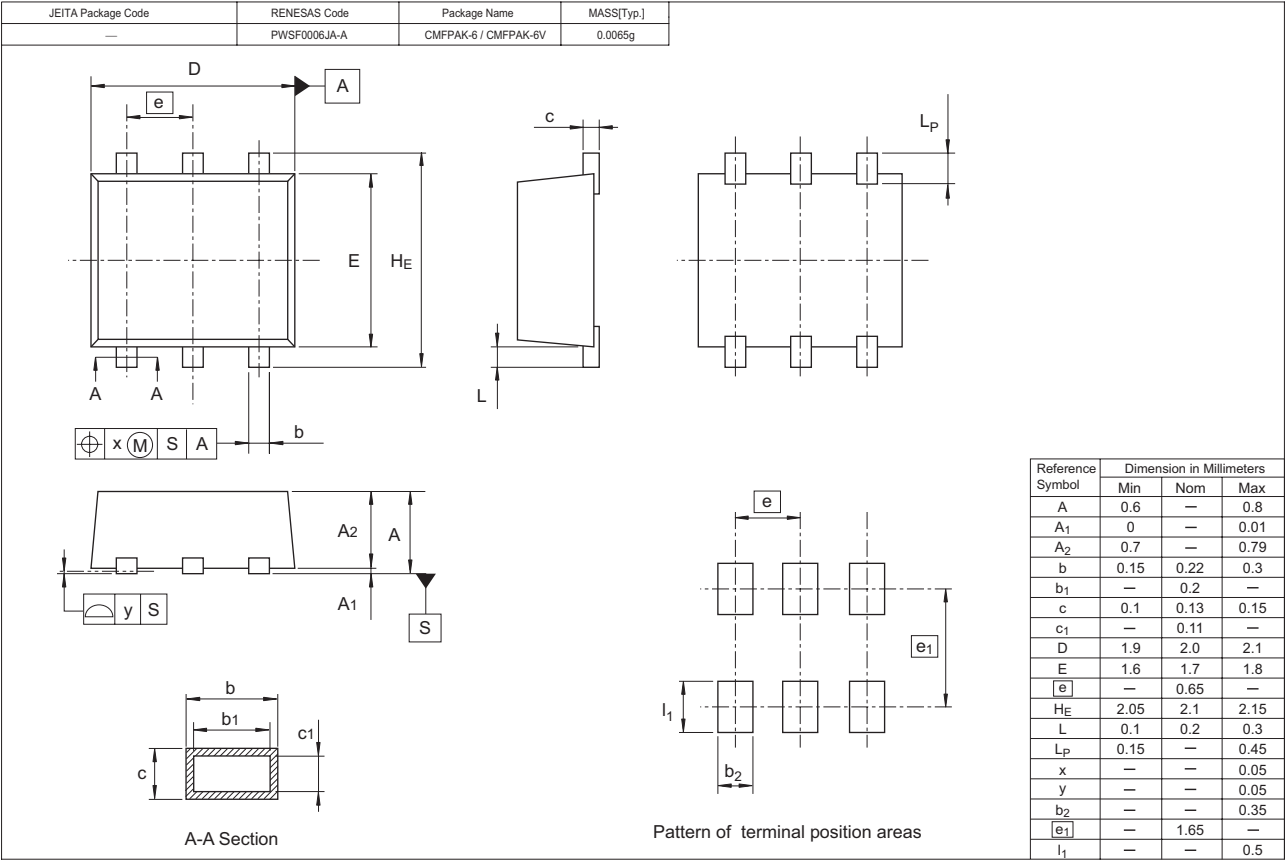
## Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT1108C-EL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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